

# MOSFET - Power, Single N-Channel, TOLL

## 40 V, 0.95 mΩ, 300 A



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## FDBL9403-F085T6

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- Small Footprint (TOLL) for Compact Design
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	$V_{DSS}$	40	V	
Gate-to-Source Voltage	$V_{GS}$	+20/-16	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$ 300	A
		$T_C = 100^\circ\text{C}$	217	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$ 159.6	W
		$T_C = 100^\circ\text{C}$	79.8	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ 50	A
		$T_A = 100^\circ\text{C}$	36	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 4.3	W
		$T_A = 100^\circ\text{C}$	2.1	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$ 3565	A	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	$I_S$	330	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 35 \text{ A}, L = 1 \text{ mH}$ )	$E_{AS}$	612.5	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	

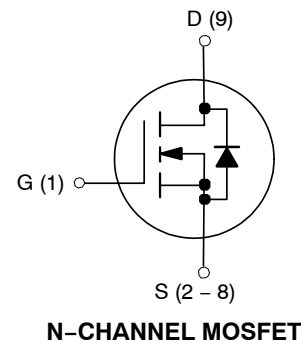
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.94	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	35	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted. Current is limited by bondwire configuration.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	0.95 mΩ @ 10 V	300 A



N-CHANNEL MOSFET



H-PSOF8L  
CASE 100CU

### ORDERING INFORMATION

Device	Package	Shipping†
FDBL9403-F085T6	H-PSOF8L (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# FDBL9403–F085T6

**Table 1. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			22		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		1	$\mu\text{A}$
			$T_J = 175^\circ\text{C}$		310	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = +20/-16 \text{ V}$			$\pm 100$	nA

**ON CHARACTERISTICS** (Note 4)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2	2.8	4	V
Threshold Temperature Coefficient	$V_{GS(th)}/T_J$			-7.1		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		0.84	0.95	m $\Omega$

**CHARGES, CAPACITANCES & GATE RESISTANCE**

Input Capacitance	$C_{iss}$	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 100 \text{ KHz}$		6985		pF
Output Capacitance	$C_{oss}$			3720		pF
Reverse Transfer Capacitance	$C_{rss}$			68		pF
Gate Resistance	$R_g$	$V_{GS} = 0.5 \text{ V}, f = 1 \text{ MHz}$		1.1		$\Omega$
Total Gate Charge	$Q_{G(tot)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$		108		nC
Threshold Gate Charge	$Q_{G(th)}$	$V_{GS} = 0 \text{ to } 2 \text{ V}$		13		nC
Gate-to-Source Gate Charge	$Q_{gs}$	$V_{DD} = 22 \text{ V}, I_D = 50 \text{ A}$		28		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$			23		nC
Plateau Voltage	$V_{GP}$			4.4		V

**SWITCHING CHARACTERISTICS** (Note 5)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10 \text{ V}, V_{DD} = 20 \text{ V}, I_D = 50 \text{ A}, R_{GEN} = 6 \Omega$		33		ns
Turn-On Rise Time	$t_r$			56		ns
Turn-Off Delay Time	$t_{d(off)}$			84		ns
Turn-Off Fall Time	$t_f$			39		ns

**DRAIN-SOURCE DIODE CHARACTERISTICS**

Source-to-Drain Diode Voltage	$V_{SD}$	$I_{SD} = 50 \text{ A}, V_{GS} = 0 \text{ V}$		0.79	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 50 \text{ A}$		84		ns
Charge Time	$t_a$			54		ns
Discharge Time	$t_b$			30		ns
Reverse Recovery Charge	$Q_{rr}$			172		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

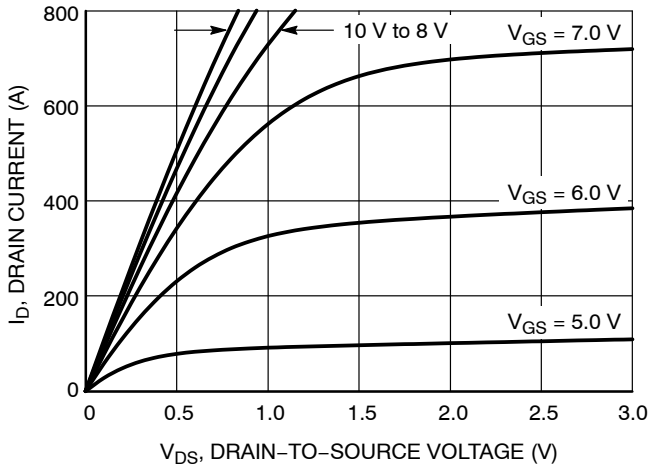


Figure 1. On-Region Characteristics

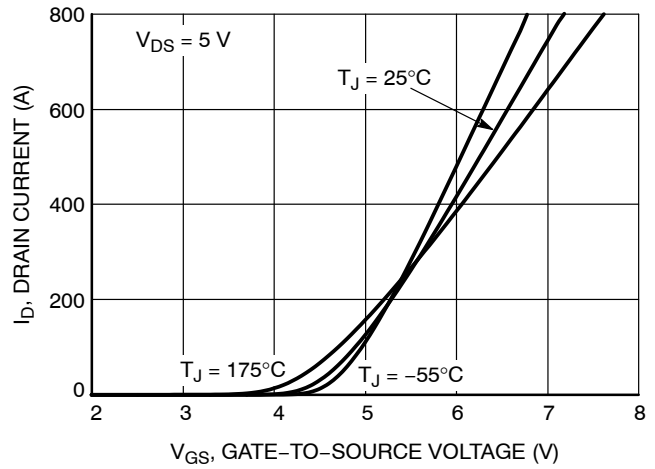


Figure 2. Transfer Characteristics

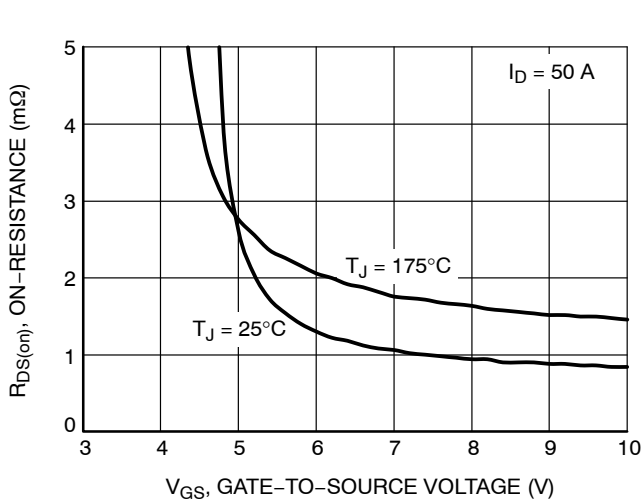


Figure 3. On-Resistance vs. Gate-to-Source Voltage

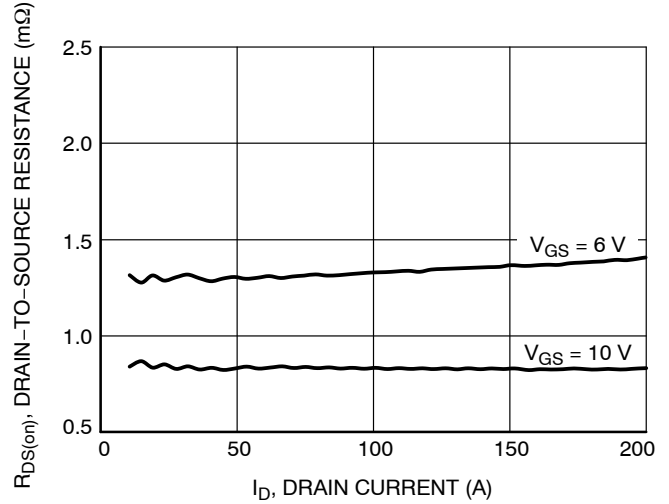


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

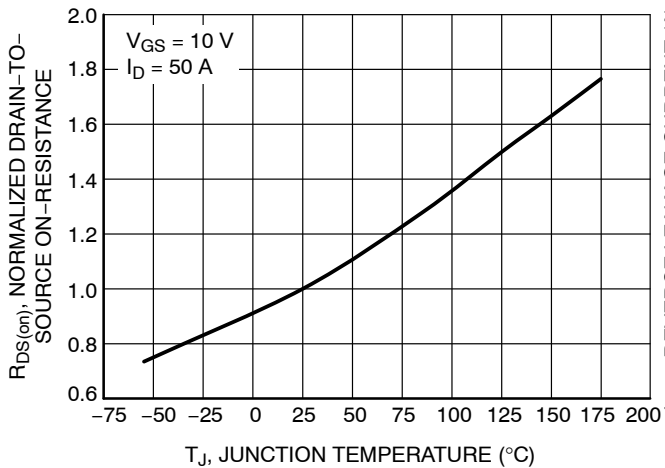


Figure 5. On-Resistance Variation with Temperature

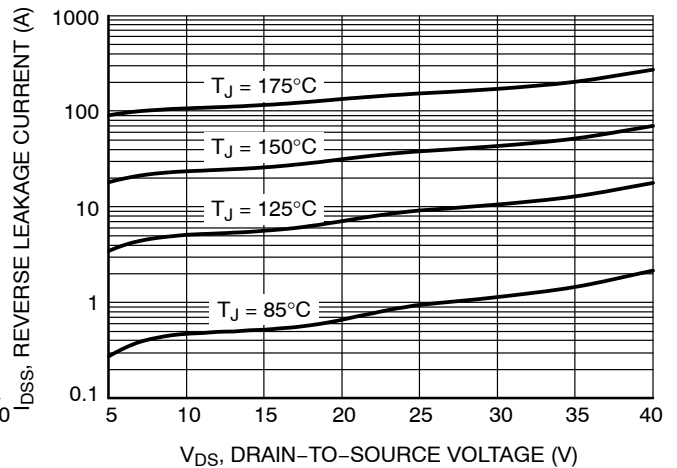


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

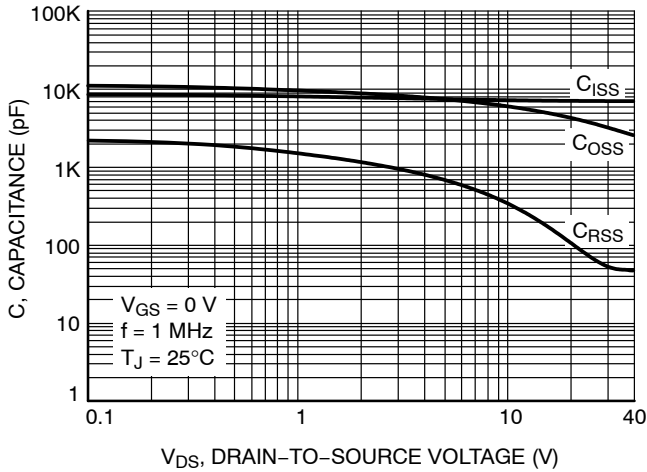


Figure 7. Capacitance Variation

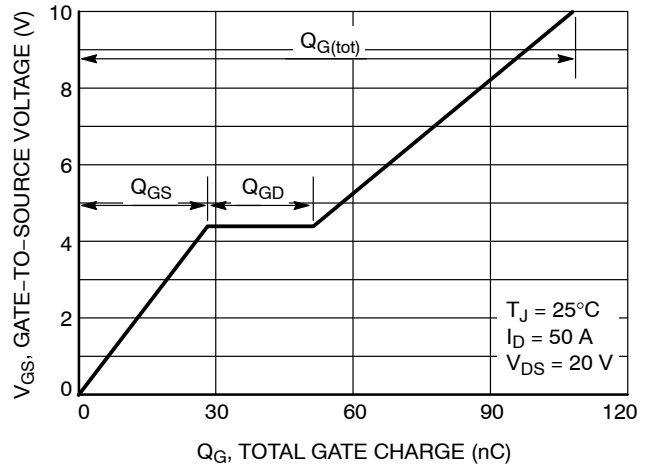


Figure 8. Gate-to-Source Voltage vs. Total Charge

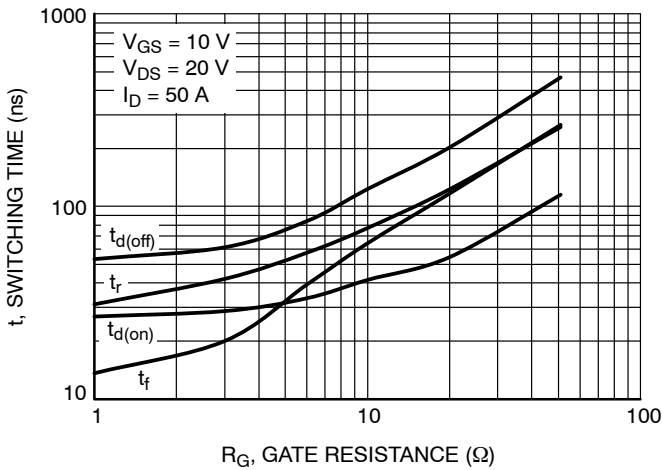


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

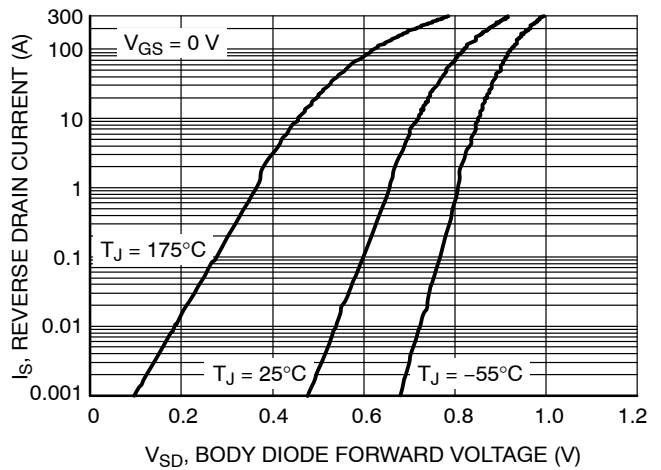


Figure 10. Diode Forward Voltage vs. Current

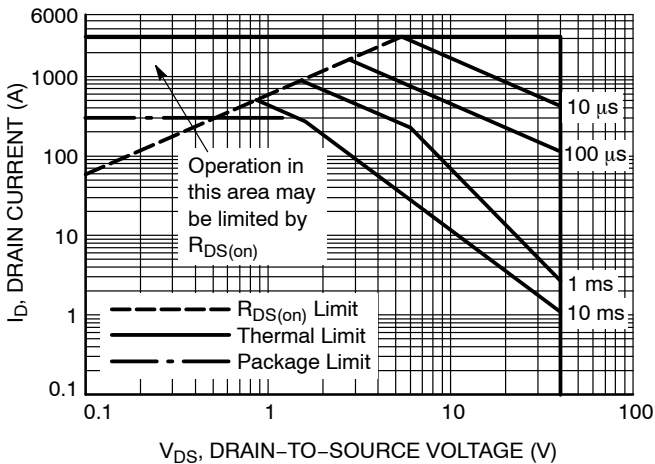


Figure 11. Maximum Rated Forward Biased Safe Operating Area

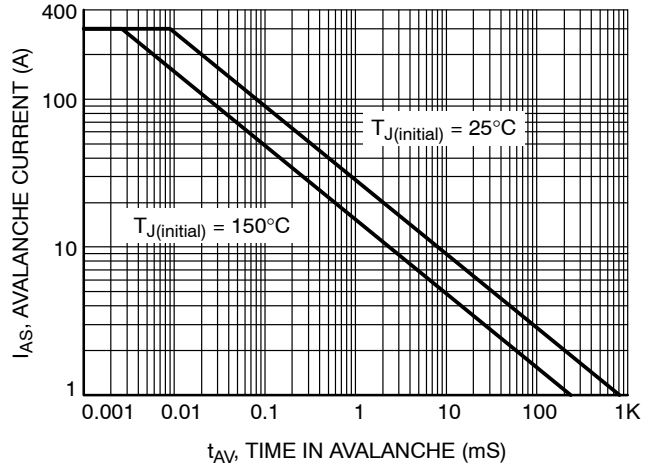


Figure 12. Maximum Drain Current vs. Time in Avalanche

TYPICAL CHARACTERISTICS

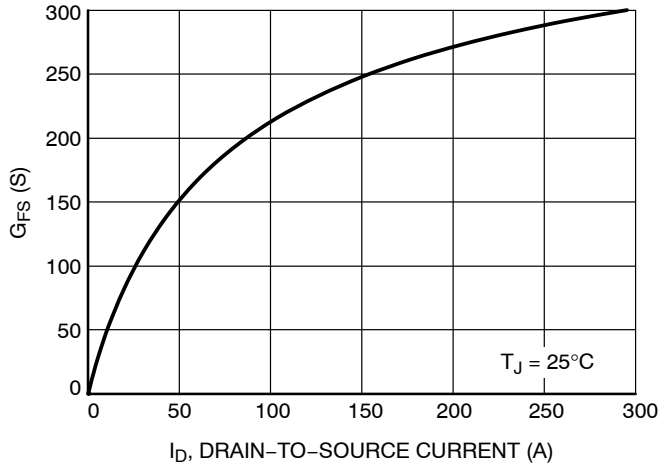


Figure 13.  $G_{FS}$  vs.  $I_D$

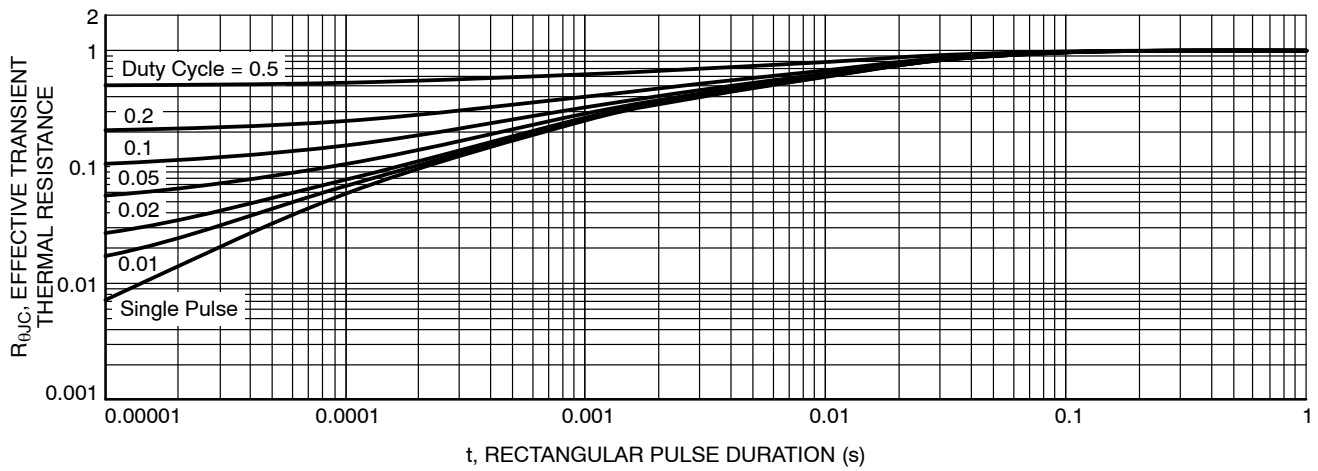
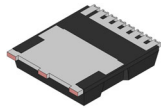


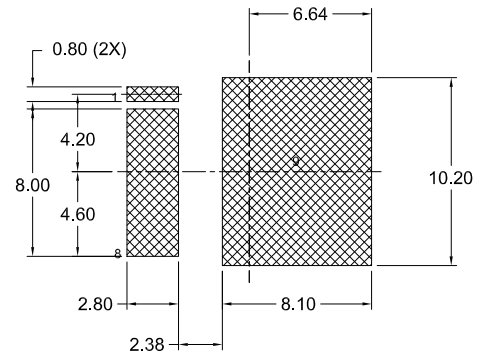
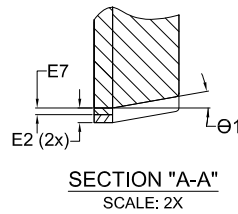
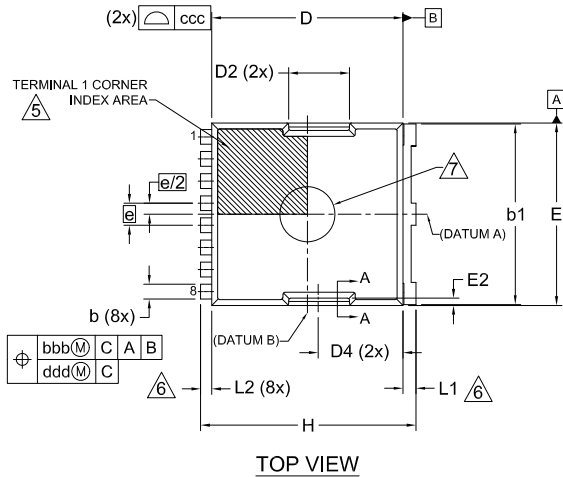
Figure 14. Transient Thermal Impedance

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

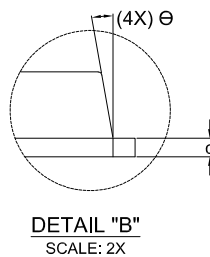
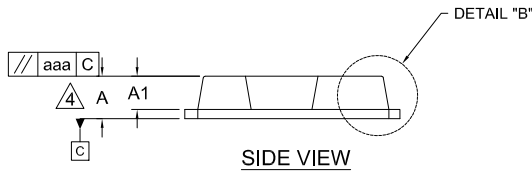


**H-PSOF8L 11.68x9.80x2.30, 1.20P**  
CASE 100CU  
ISSUE E

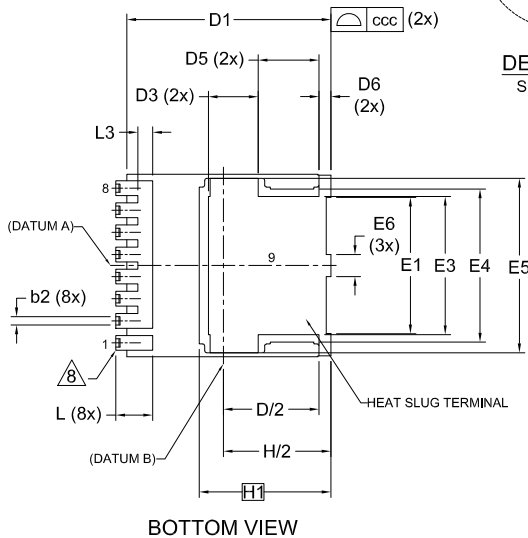
DATE 31 MAY 2024



\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

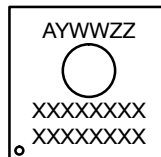


- NOTES:**
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
  2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
  3. "e" REPRESENTS THE TERMINAL PITCH.
  4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
  5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
  6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
  7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
  8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



### GENERIC MARKING DIAGRAM\*

A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code  
XXXX = Specific Device Code



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.47
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
θ	10° REF		
θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

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